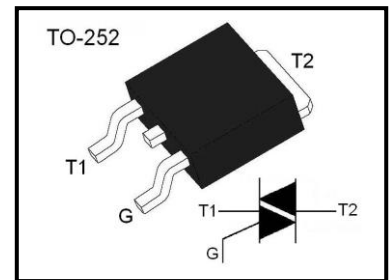


## Triacs

### General Description

Glass passivated triacs in a plastic envelope, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.



### Absolute Maximum Rating (Ta=25°C)

Limiting values in accordance with the Absolute Maximum System

Parameter	Symbol	Conditions	Ratings	Unit	
Repetitive peak off-state voltages	$V_{RRM}$ $V_{DRM}$		500 600 800	V	
On-State RMS Current	$I_{T(RMS)}$	full sine wave; $T_{mb} \leq 51$ °C	4	A	
Non-repetitive peak on-state current	$I_{TSM}$	full sine wave; $T_j = 25$ °C prior to surge	$t = 20$ ms	25	A
			$t = 16.7$ ms	27	
$I^2t$ for fusing	$I^2t$	$t = 20$ ms	3.1	A <sup>2</sup> s	
Repetitive rate of rise of on-state current after triggering	$dI_T/dt$	$I_{TM} = 6$ A; $I_G = 0.2$ A; $dI_G/dt = 0.2$ A/ $\mu$ s	T2+ G+	50	A/ $\mu$ s
			T2+ G-	50	
			T2- G-	50	
			T2- G+	10	
Peak gate current	$I_{GM}$		2	A	
Peak Gate Voltage	$V_{GM}$		5	V	
Peak gate power	$P_{GM}$		5	W	
Average gate power	$P_{G(AV)}$	over any 20 ms period	0.5	W	
Operating junction temperature	$T_j$		-40 ~125	°C	
Storage Temperature	$T_{stg}$		-40 ~150	°C	

### Thermal Resistances

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Thermal resistance junction to solder point	$R_{th\ j-sp}$	full cycle half cycle	-		3.0 3.7	°C/W
Thermal resistance junction to ambient	$R_{th\ j-a}$	in free air	-	75		°C/W

**Static Characteristics** ( $T_j = 25\text{ }^\circ\text{C}$  unless otherwise stated)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Gate trigger current	$I_{GT}$	$V_D = 12\text{ V}$ , $I_T = 0.1\text{ A}$	T2+ G+			10	mA
			T2+ G-			10	
			T2- G-			10	
			T2- G+			25	
Latching current	$I_L$	$V_D = 12\text{ V}$ , $I_{GT} = 0.1\text{ A}$	T2+ G+			15	mA
			T2+ G-			20	
			T2- G-			15	
			T2- G+			20	
Holding current	$I_H$	$V_D = 12\text{ V}$ , $I_{GT} = 0.1\text{ A}$			15	mA	
On-state voltage	$V_T$	$I_T = 5\text{ A}$		1.4	1.7	V	
Gate trigger voltage	$V_{GT}$	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$		0.7	1.5	V	
			0.25				
Off-state leakage current	$I_D$	$V_D = V_{DRM(max)}$ ; $T_j = 125\text{ }^\circ\text{C}$			0.5	mA	

**Dynamic Characteristics**  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise stated

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Critical rate of rise of off-state voltage	$dV_D/dt$	$V_{DM} = 67\% V_{DRM(max)}$ ; $T_j = 125\text{ }^\circ\text{C}$ Vexponential waveform; gate open circuit		0		V/ $\mu\text{s}$
Gate controlled turn-on time	tgt	$I_{TM} = 6\text{ A}$ ; $I_G = 0.1\text{ A}$ ; $V_D = V_{DRM(max)}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$ ;		2		$\mu\text{s}$

Typical Characteristics

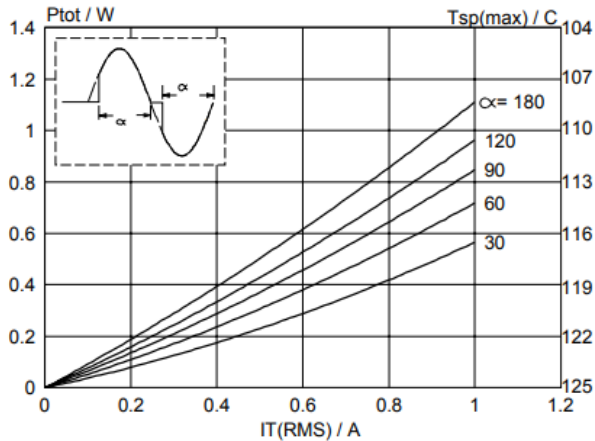


Fig.1. Maximum on-state dissipation, Ptot, versus rms on-state current, IT(RMS), where α = conduction angle.

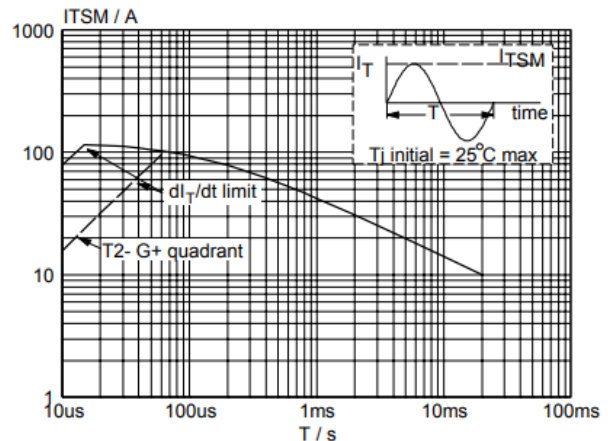


Fig.2. Maximum permissible non-repetitive peak on-state current ITSM, versus pulse width tp, for sinusoidal currents, tp ≤ 20ms.

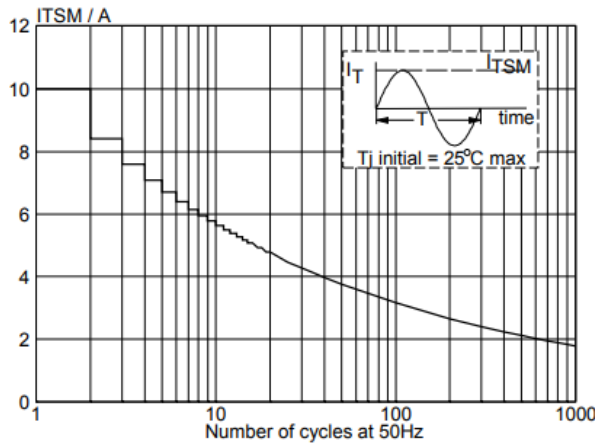


Fig.3. Maximum permissible non-repetitive peak on-state current ITSM, versus number of cycles, for sinusoidal currents, f = 50 Hz.

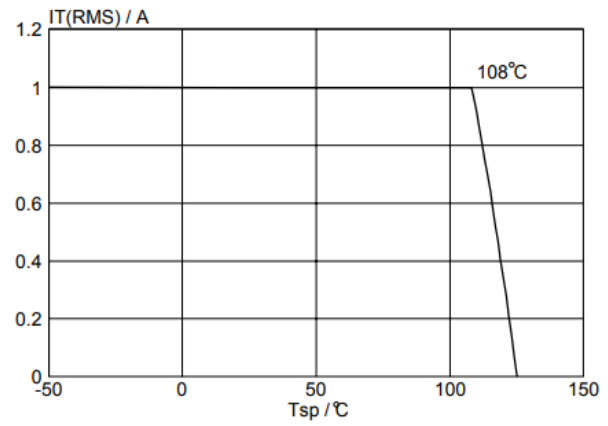


Fig.4. Maximum permissible rms current IT(RMS), versus solder point temperature Tsp.

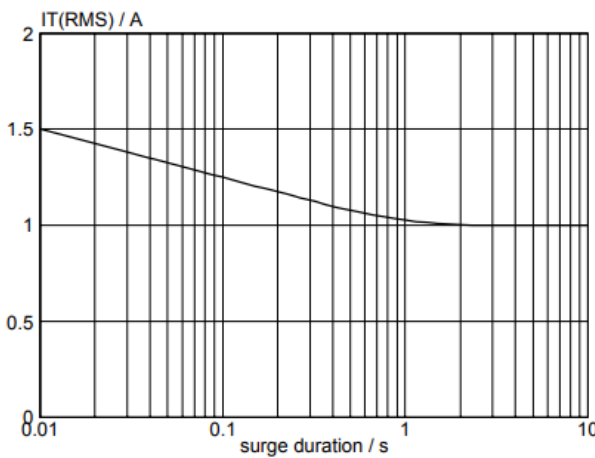


Fig.5. Maximum permissible repetitive rms on-state current IT(RMS), versus surge duration, for sinusoidal currents, f = 50Hz; Tsp ≤ 108°C.

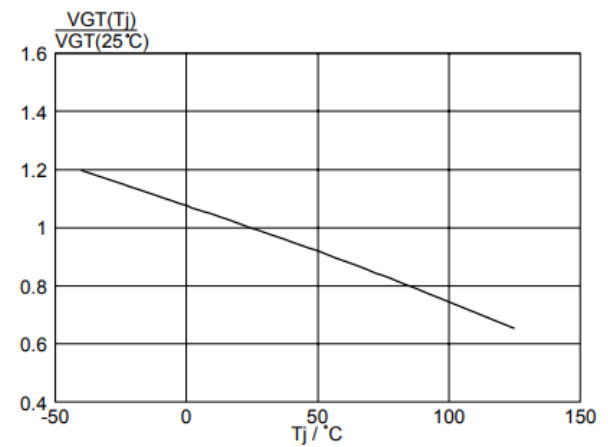


Fig.6. Normalised gate trigger voltage VGT(Tj)/VGT(25°C), versus junction temperature Tj.

Typical Characteristics

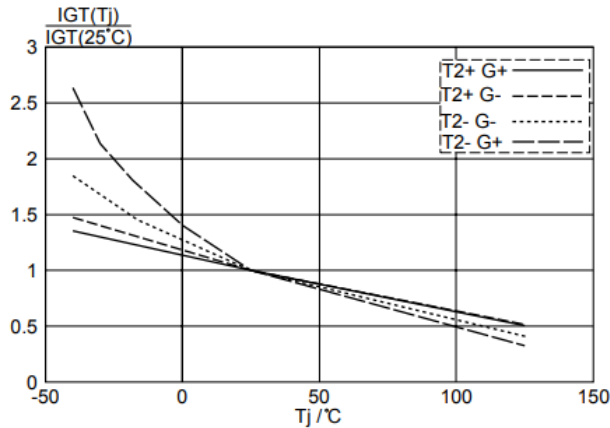


Fig.7. Normalised gate trigger current  $I_{GT}(T_j) / I_{GT}(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

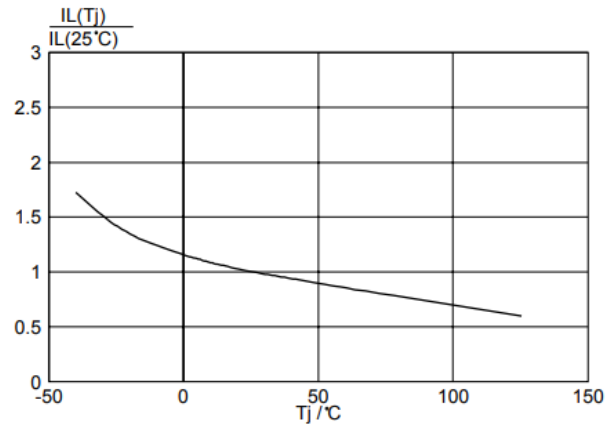


Fig.8. Normalised latching current  $I_L(T_j) / I_L(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

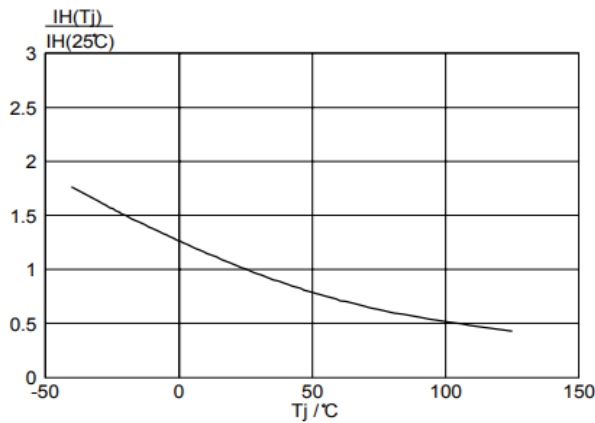


Fig.9. Normalised holding current  $I_H(T_j) / I_H(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

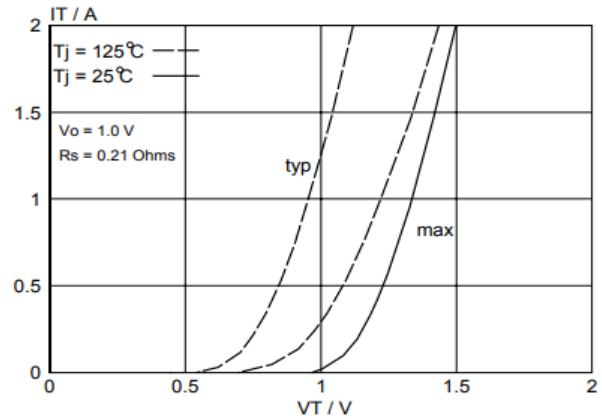


Fig.10. Typical and maximum on-state characteristic.

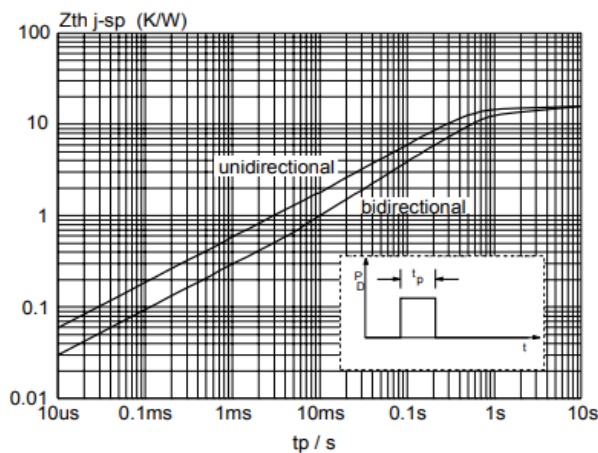


Fig.11. Transient thermal impedance  $Z_{th\ j-sp}$ , versus pulse width  $t_p$ .

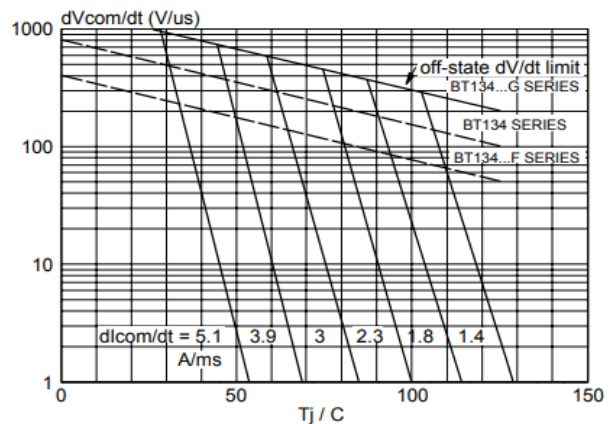
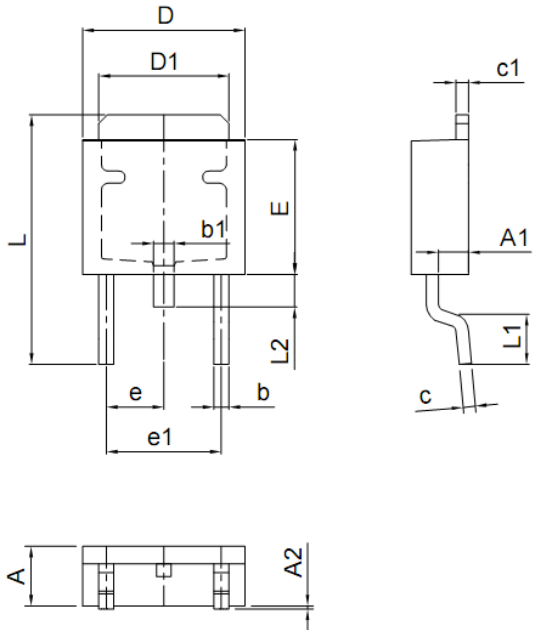


Fig.12. Typical commutation  $dV/dt$  versus junction temperature, parameter commutation  $dI_T/dt$ . The triac should commute when the  $dV/dt$  is below the value on the appropriate curve for pre-commutation  $dI_T/dt$ .

Package Dimensions



Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.50	0.087	0.094
A1	1.00	1.40	0.039	0.055
A2	0.00	0.15	0.000	0.006
b	0.50	0.70	0.020	0.028
b1	0.70	0.90	0.028	0.035
c	0.40	0.60	0.016	0.024
c1	0.40	0.60	0.016	0.024
D	6.20	6.70	0.244	0.264
D1	5.10	5.50	0.201	0.217
E	5.50	6.00	0.217	0.236
e	2.20	2.40	0.087	0.094
e1	4.40	4.80	0.173	0.189
L	9.70	10.40	0.382	0.409
L1	1.40	1.70	0.055	0.063
L2	0.60	1.20	0.024	0.047